What Is Claimed Is:

1. A method of fabricating a liquid crystal display device, comprising the following steps:

forming a gate line on a first substrate;

forming a data line crossing the gate line;

forming a switching element connected to the gate line and the data line;

forming a pixel electrode connected to the switching element;

forming a black matrix on a second substrate using a sputter, wherein the sputter includes a shield mask having an open portion having dimensions larger than or equal to size dimensions of the second substrate;

forming a color filter layer on the black matrix;

forming a common electrode on the color filter layer;

attaching the first and second substrates such that the pixel electrode faces the common electrode; and

forming a liquid crystal layer between the pixel electrode and the common electrode.

2. The method of claim 1, wherein the black matrix includes chromium (Cr) and chromium oxide (CrOx).

3. The method of claim 2, wherein the gate line includes one of aluminum (Al), aluminum neodymium (AlNd), chromium (Cr), copper (Cu), molybdenum (Mo), tungsten (W) and titanium (Ti).

4. The method of claim 3, wherein the gate line is formed by using a sputter, wherein the sputter includes a shield mask having an open portion having dimensions larger than or equal to size dimensions of the first substrate.

5. The method of claim 4, wherein the data line includes one of aluminum (Al), aluminum neodymium (AlNd), chromium (Cr), copper (Cu), molybdenum (Mo), tungsten (W) and titanium (Ti).

6. The method of claim 5, wherein the data line is formed by using a sputter, wherein the sputter includes a shield mask having an open portion having dimensions larger than or equal to size dimensions of the first substrate.

7. The method of claim 6, wherein the pixel electrode includes one of indium-tin-oxide (ITO) and indium-zinc-oxide (IZO).

8. The method of claim 7, wherein the pixel electrode is formed by using a sputter, wherein the sputter includes a shield mask having an open portion having dimensions larger than or equal to size dimensions of the first substrate.

9. The method of claim 8, wherein the common electrode includes one of indium-tin-oxide (ITO) and indium-zinc-oxide (IZO).

10. The method of claim 9, wherein the common electrode is formed by using a sputter, wherein the sputter includes a shield mask having an open portion having dimensions larger than or equal to size dimensions of the second substrate.

11. A sputter for a fabricating process of a liquid crystal display device, comprising:

a chamber;

a susceptor in the chamber, a substrate being loaded on the susceptor;

a platen under the susceptor, the platen adjusting a height of the susceptor;

a target over the susceptor;

a magnet over the target; and

a shield mask between the substrate and the target, the shield mask having an open portion having dimensions larger than or equal to size dimensions of the substrate.

12. The sputter of claim 11, wherein the target includes one of chromium (Cr), chromium oxide (CrOx), aluminum (Al), aluminum neodymium (AlNd), copper (Cu), molybdenum (Mo), tungsten (W), titanium (Ti), indium-tin-oxide (ITO) and indium-zinc-oxide (IZO).

13. A shield mask for a sputter including a chamber, a susceptor and a target in the chamber, wherein the shield mask is disposed between the target and a substrate loaded on the susceptor and has an open portion with dimensions larger than or equal to size dimensions of the substrate.

14. A method of sputtering a metal layer onto a substrate, comprising the following steps:

providing a sputtering chamber having a susceptor and a target therein;

providing a shield between the susceptor and the target, the shield having an opening therein;

placing a substrate on the susceptor below the shield, the substrate having size dimensions smaller than or equal to size dimensions of the opening of the shield; and

sputtering a metal layer onto the substrate.

15. The method of claim 14, wherein the metal layer includes one of chromium (Cr), chromium oxide (CrOx), aluminum (Al), aluminum neodymium (AlNd), copper (Cu), molybdenum (Mo), tungsten (W), titanium (Ti), indium-tin-oxide (ITO) and indium-zinc-oxide (IZO).

16. The method of claim 14, wherein the metal layer is a gate line of a liquid crystal display device.

17. The method of claim 14, wherein the metal layer is a data line of a liquid crystal display device.

18. The method of claim 14, wherein the metal layer is a black matrix of a liquid crystal display device.

19. The method of claim 14, wherein the metal layer is a pixel electrode of a liquid crystal display device.

20. The method of claim 14, wherein the metal layer is a common electrode of a liquid crystal display device.